



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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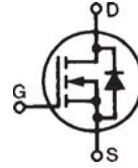


HiPerRF™

Power MOSFETs

F-Class: MegaHertz Switching

IXFH12N50F IXFT12N50F

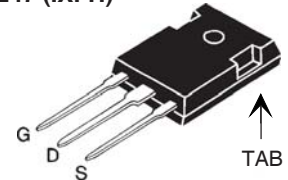


N-Channel Enhancement Mode
Avalanche Rated, Low Q_g , Low
Intrinsic R_g , High dV/dt , Low t_{rr}

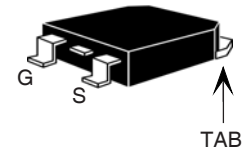
$V_{DSS} = 500V$
 $I_{D25} = 12A$
 $R_{DS(on)} \leq 400m\Omega$
 $t_{rr} \leq 250ns$

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ C$ to $150^\circ C$	500	V
V_{DGR}	$T_J = 25^\circ C$ to $150^\circ C$, $R_{GS} = 1M\Omega$	500	V
V_{GSS}	Continuous	± 20	V
V_{GSM}	Transient	± 30	V
I_{D25}	$T_C = 25^\circ C$	12	A
I_{DM}	$T_C = 25^\circ C$, Pulse Width Limited by T_{JM}	48	A
I_{AR}	$T_C = 25^\circ C$	12	A
E_{AS}	$T_C = 25^\circ C$	300	mJ
dV/dt	$I_S \leq I_{DM}$, $di/dt \leq 100A/\mu s$, $V_{DD} \leq V_{DSS}$ $T_J \leq 150^\circ C$, $R_G = 2\Omega$	20	V/ns
P_D	$T_C = 25^\circ C$	180	W
T_J		-55 ... +150	$^\circ C$
T_{JM}		150	$^\circ C$
T_{stg}		-55 ... +150	$^\circ C$
T_L	Maximum Lead Temperature for Soldering	300	$^\circ C$
T_{SOLD}	Plastic Body for 10s	260	$^\circ C$
M_d	Mounting Torque (TO-247)	1.13/10	Nm/lb.in.
Weight	TO-247	6	g
	TO-268	4	g

TO-247 (IXFH)



TO-268 (IXFT)



G = Gate D = Drain
S = Source TAB = Drain

Features

- RF capable MOSFETs
- Double metal process for low gate resistance
- Low $R_{DS(ON)}$ DHMOS™ process
- Rugged polysilicon gate cell structure
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
- Fast intrinsic rectifier

Applications

- DC-DC converters
- Switched-mode and resonant-mode power supplies, >500kHz switching
- DC choppers
- 13.5 MHz industrial applications
- Pulse generation
- Laser drivers
- RF amplifiers

Advantages

- Space savings
- High power density

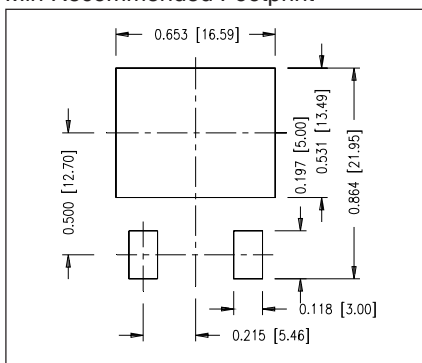
Symbol	Test Conditions ($T_J = 25^\circ C$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0V$, $I_D = 250\mu A$	500		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 2.5mA$	3.0		5.5 V
I_{GSS}	$V_{GS} = \pm 20V$, $V_{DS} = 0V$			± 100 nA
I_{DSS}	$V_{DS} = 0.8 \cdot V_{DSS}$			50 μA
	$V_{GS} = 0V$ $T_J = 125^\circ C$			1.5 mA
$R_{DS(on)}$	$V_{GS} = 10V$, $I_D = 0.5 \cdot I_{D25}$, Note 1			400 m Ω

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$V_{DS} = 10\text{V}, I_D = 0.5 \cdot I_{D25}$, Note	6	10	S
C_{iss}	$V_{GS} = 0\text{V}, V_{DS} = 25\text{V}, f = 1\text{MHz}$		1870	pF
C_{oss}			290	pF
C_{rss}			90	pF
$t_{d(on)}$	Resistive Switching Times $V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$ $R_G = 4.7\Omega$ (External)		11	ns
t_r			14	ns
$t_{d(off)}$			28	ns
t_f			8	ns
$Q_{g(on)}$	$V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$		54	nC
Q_{gs}			18	nC
Q_{gd}			25	nC
R_{thJC}	(TO-247)			0.65 $^\circ\text{C/W}$
R_{thCS}			0.21	$^\circ\text{C/W}$

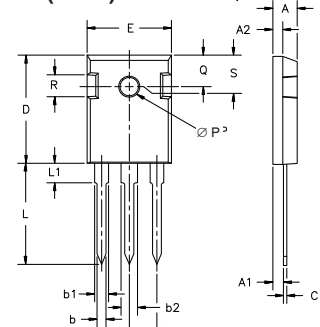
Source-Drain Diode		Characteristic Values		
$T_J = 25^\circ\text{C}$ Unless Otherwise Specified)		Min.	Typ.	Max.
I_S	$V_{GS} = 0\text{V}$			12 A
I_{SM}	Repetitive, Pulse Width Limited by T_{JM}			48 A
V_{SD}	$I_F = I_S, V_{GS} = 0\text{V}$, Note 1			1.5 V
t_{rr}	$I_F = 12\text{A}, -di/dt = 100\text{A}/\mu\text{s}$			250 ns
Q_{RM}			0.8	μC
I_{RM}	$V_R = 100\text{V}, V_{GS} = 0\text{V}$		6.5	A

Note: 1. Pulse test, $t \leq 300 \mu\text{s}$, duty cycle $d \leq 2\%$

Min Recommended Footprint

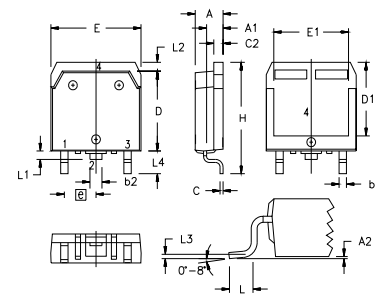


TO-247 (IXFH) Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A ₁	2.2	2.54	.087	.102
A ₂	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b ₁	1.65	2.13	.065	.084
b ₂	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
ØP	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	.242	BSC

TO-268 Outline



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.193	.201	4.90	5.10
A1	.106	.114	2.70	2.90
A2	.001	.010	0.02	0.25
b	.045	.057	1.15	1.45
b2	.075	.083	1.90	2.10
C	.016	.026	0.40	0.65
C2	.057	.063	1.45	1.60
D	.543	.551	13.80	14.00
D1	.488	.500	12.40	12.70
E	.624	.632	15.85	16.05
E1	.524	.535	13.30	13.60
e	.215 BSC		5.45 BSC	
H	.736	.752	18.70	19.10
L	.094	.106	2.40	2.70
L1	.047	.055	1.20	1.40
L2	.039	.045	1.00	1.15
L3	.010 BSC		0.25 BSC	
L4	.150	.161	3.80	4.10

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	